

WHAT IS CLAIMED IS:

1. A semiconductor substrate stock/transfer vessel,
which is an openable/closeable sealed vessel used in a
semiconductor device manufacturing process and adapted to
store or transfer a semiconductor substrate,

5 wherein said vessel incorporates at least one
adsorbent capable of adsorbing an organic substance, and
said adsorbent is mounted detachably.

2. A vessel according to claim 1, wherein said
10 vessel incorporates a semiconductor substrate carrier
having a plurality of slots each capable of holding one
semiconductor substrate, so that a plurality of
semiconductor substrates are stored while being held by
said semiconductor substrate carrier.

15 3. A vessel according to claim 1, wherein said
adsorbent is a silicon wafer with a surface coated with an
adsorbing agent.

4. A vessel according to claim 3, wherein said
adsorbing agent is active carbon or an ion-exchange resin.

20 5. A vessel according to claim 1, wherein said
adsorbent is a silicon wafer with a surface having a Si-F
bond.

3 6. A vessel according to claim 2, wherein said
adsorbent is mounted in an empty slot of said
25 semiconductor substrate carrier.

- 4 ~~7~~. A vessel according to claim 1, wherein said adsorbent is mounted in a space defined between an inner wall of said stock/transfer vessel and an outer wall of said semiconductor substrate carrier.
- 5 ~~8~~. A vessel according to claim 1, wherein said adsorbent is made of active carbon or an ion-exchange resin.
- ~~9~~. A vessel according to claim 1, wherein said adsorbent is made of active carbon or an ion-exchange resin.
- 10 ~~10~~. A method of manufacturing a semiconductor device wherein a semiconductor substrate is stored in a stock/transfer vessel incorporating at least one adsorbent capable of adsorbing an organic substance during an operation wait time between respective steps of manufacturing said semiconductor device, said adsorbent being mounted detachably.
- 15 ~~11~~ 7 ~~11~~. A method according to claim 10, wherein the steps of manufacturing said semiconductor device include the
- 20 step of forming a gate oxide film, the step of forming a polysilicon film, and the step of forming a contact hole.
- 8 ~~12~~. A method according to claim 10, wherein said vessel incorporates a semiconductor substrate carrier having a plurality of slots each capable of holding one
- 25 semiconductor substrate, and a plurality of semiconductor

substrates are stored while being held by said semiconductor substrate carrier.

~~13.~~ A method according to claim 10, wherein said adsorbent is a silicon wafer with a surface coated with an
5 adsorbing agent.

~~14.~~ A method according to claim 13, wherein said adsorbing agent is active carbon or an ion-exchange resin.

~~15.~~ A method according to claim 10, wherein said adsorbent is a silicon wafer with a surface having a Si-F
10 bond.

~~16.~~ A method according to claim 12, wherein said adsorbent is mounted in an empty slot of said semiconductor substrate carrier.

~~17.~~ A method according to claim 10, wherein said
15 adsorbent is mounted in a space defined between an inner wall of said stock/transfer vessel and an outer wall of said semiconductor substrate carrier.

~~18.~~ A method according to claim 10, wherein said adsorbent is made of active carbon or an ion-exchange
20 resin.